1 IGBT mold types

- High speed switching
- Low saturation voltage
- Voltage drive method permits low power drive
- Suited for high frequency power supplies, such as microwave ovens
- When using these IGBTs, FUJI's fast recovery diode ERD60-100 is required.

Device type	V_{CES} Volts	V_{GES} Volts	I_C cont. Amps.	P_C Watts	V_{CE}(sat) Max. Volts	Switching time (Max.) t_{on} µsec.	t_{off} µsec.	t_f µsec.	Package	Net mass Grams
1MBH60-090	900	±20	60	260	3.2	—	—	1.0	TO3PL	9.5
1MBH60-100	1000	±20	60	260	3.4	—	—	1.0	TO3PL	9.5
1MBH65-090	900	±20	65	260	3.0	—	—	1.0	TO3PL	9.5
1MBH65-100	1000	±20	65	300	3.2	—	—	1.0	TO3PL	9.5

Fast recovery diode for IGBT

Device type	V_{RRM} Volts	I_F Amps	P_D Watts	I_R µA	V_F Volts	t_{rr} µsec.	R_{th}(j-c) °C/W	Package	Net mass Grams
ERD60-100	1000	15	40	100	2.5	3.0	3.1	TO220AB	2
ERD65-090	900	30	50	100	1.4	4.4	2.5	TO3PF	6.0

2 600 volts class IGBT modules/High speed switching (L series)

- High speed switching
- Voltage drive method permits low power drive

Device type	V_{CES} Volts	V_{GES} Volts	I_C cont. Amps.	P_C Watts	V_{CE}(sat) Max. Volts	Switching time (Max.) t_{on} µsec.	t_{off} µsec.	t_f µsec.	Package	Net mass Grams	Equivalent circuit Page 53
2MBI50L-060	600	±20	50	250	3.5	0.8	1.0	0.35	M218	210	Fig. 2
2MBI75L-060	600	±20	75	325	3.5	0.8	1.0	0.35	M218	210	Fig. 2
2MBI100L-060	600	±20	100	400	3.5	0.8	1.0	0.35	M218	210	Fig. 2
2MBI150L-060	600	±20	150	600	3.5	0.8	1.0	0.35	M219	340	Fig. 2
2MBI150LB-060	600	±20	150	600	3.5	0.8	1.0	0.35	M221	250	Fig. 2
2MBI200L-060	600	±20	200	800	3.5	0.8	1.0	0.35	M219	340	Fig. 2
2MBI200LB-060	600	±20	200	800	3.5	0.8	1.0	0.35	M221	250	Fig. 2
2MBI300L-060	600	±20	300	1200	3.5	0.8	1.0	0.35	M217	410	Fig. 2
2MBI300LB-060	600	±20	300	1200	3.5	0.8	1.0	0.35	M225	380	Fig. 2
2MBI400L-060	600	±20	400	1600	3.5	0.8	1.0	0.35	M225	380	Fig. 2
1MBI300L-060	600	±20	300	1200	3.5	0.8	1.0	0.35	M116	415	Fig. 1
1MBI400L-060	600	±20	400	1600	3.5	0.8	1.0	0.35	M116	415	Fig. 1
1MBI600LP-060	600	±20	600	2000	3.5	1.0	1.2	0.5	M121	370	Fig. 1
1MBI600LN-060	600	±20	600	2000	3.5	1.0	1.2	0.5	M122	370	Fig. 1

Letter symbols

V_{CES}: Collector-to-emitter rated voltage (Gate-to-emitter short-circuited)
V_{GES}: Gate-to-emitter rated voltage (Collector-to-emitter short-circuited)
I_C: Rated collector current
P_C: Maximum power dissipation
V_{CE} (sat): Collector-to-emitter saturation voltage
t_{on}: Turn-on time
t_{off}: Turn-off time
t_f: Fall time